AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-2. (canceled)

3. (currently amended) A production method of ~~containing fullerene~~ encapsulating-fullerene or ~~containing-nanotube~~ encapsulating-nanotube material film, the method comprises:

generating plasma including ~~containment~~ encapsulation target ions and collision ions having the same polarity as said ~~containment~~ encapsulation target ions;

irradiating said plasma toward a deposition-assistance substrate on which fullerene or nanotube are deposited, by applying a bias voltage of a polarity opposite to that of said ~~containment~~ encapsulation target ions to said deposition-assistance substrate, to thereby provide said ~~containment~~ encapsulation target ions and said collision ions with acceleration energies, respectively; and

colliding said collision ions with fullerene molecules or nanotube molecules, to thereby cause said fullerene molecules or nanotube molecules to ~~internally contain~~ encapsulate said ~~containment~~ encapsulation target ions, respectively.

4. (previously presented) The production method of claim 3, further comprising:

depositing said fullerene molecules or nanotube molecules on said deposition-assistance substrate, simultaneously with the irradiation of said plasma toward said deposition-assistance substrate.

5. (previously presented) The production method of claim 3, further comprising:

irradiating said plasma onto said fullerene molecules or nanotube molecules previously deposited on said deposition-assistance substrate.

6. (currently amended) A production method of ~~containing-fullerene~~ encapsulating-fullerene or ~~containing-nanotube~~ encapsulating-nanotube material film, the method comprising:

generating plasma including collision ions;

irradiating said plasma toward fullerene or nanotube previously deposited on a deposition-assistance substrate;

simultaneously therewith, shooting vapor comprising ~~containment~~ encapsulation target molecules toward said fullerene or nanotube;

colliding said collision ions with fullerene molecules or nanotube molecules, to thereby cause fullerene molecules or nanotube molecules to ~~internally contain~~ encapsulate said ~~containment~~ encapsulation target molecules.

7. (previously presented) The production method of claim 6, further comprising:

transporting said generated plasma by a magnetic field to thereby irradiate said plasma toward said deposition-assistance substrate.

8. (canceled)

9. (currently amended) The production method of claim 3, wherein said ~~implantation target ions or said containment~~ encapsulation target ions are alkali metal ions, nitrogen ions, or halogen ions.

10. (currently amended) The production method of claim 6, wherein said ~~containment target substance is~~ encapsulation target molecules are TTF, TDAE, TMTSF, pentacene, tetracene, anthracene, TCNQ, Alq_3, or F_4TCNQ.

11. (previously presented) The production method of claim 3, wherein said collision ions each have a diameter of 3.0 Å or larger.

12. (previously presented) The production method of claim 11, wherein said collision ions are fullerene positive ions or fullerene negative ions, respectively.

13. (currently amended) A production apparatus of ~~containing fullerene~~ encapsulating-fullerene or ~~containing-nanotube~~ encapsulating-nanotube comprising:

a vacuum vessel;

plasma generation means for generating plasma including ~~implantation~~ encapsulation target ions and collision ions having the same polarity as said ~~containment~~ encapsulation target ions;

a deposition-assistance substrate having ~~for depositing~~ fullerene or nanotube deposited thereon;

magnetic field generation means for transporting and irradiating said plasma to said deposition-assistance substrate; and

a bias power supply configured to apply a bias voltage to said deposition-assistance substrate.

14. (previously presented) The production apparatus of claim 13, wherein said electric potential body comprises electroconductive wires in a lattice pattern.

15. (currently amended) A production apparatus of ~~containing-fullerene~~ encapsulating-fullerene or ~~containing-nanotube~~ encapsulating-nanotube comprising:

a vacuum vessel;

plasma generation means for generating plasma including ~~containment~~ encapsulation target ions;

collision ion generation means for generating collision ions;

a deposition-assistance substrate having ~~for depositing~~ fullerene or nanotube deposited thereon;

magnetic field generation means for transporting and irradiating said plasma to said deposition-assistance substrate; and

a bias power supply configured to apply a bias voltage to said deposition-assistance substrate.

16. (currently amended) A production apparatus of ~~containing-fullerene~~ encapsulating-fullerene or ~~containing-nanotube~~ encapsulating-nanotube comprising:

a vacuum vessel;

plasma generation means for generating plasma including collision ions;

a deposition-assistance substrate having ~~for depositing~~ fullerene or nanotube deposited thereon;

magnetic field generation means for transporting and irradiating said plasma to said deposition-assistance substrate;

~~containment~~ encapsulation target molecule shooting means for shooting vapor including ~~containment~~ encapsulation target molecules to said deposition-assistance substrate; and

a bias power supply configured to apply a bias voltage to said deposition-assistance substrate.

17. (currently amended) The production method of claim 3, further comprising:

measuring an electric current flowing between the deposition-assistance substrate and a bias power supply for

applying the bias voltage thereto, to thereby measure the density of the ~~containment~~ encapsulation target ions.